

Product Overview

NSI22C12 is a high-speed isolated comparator with output separated from input based on the NOVOSENSE capacitive isolation technology Adaptive OOK®. The NSI22C12 is an isolated window comparator with open-drain output and latch enable function. The short response time of NSI22C12 makes it highly suitable for over-current or over-voltage protection application. The high common-mode transient immunity ensures that the device is able to provide accurate protection even in the presence of high-power switching such as in motor control applications.

NSI22C12 have an adjustable input reference threshold of 20mV~ 320mV and the window threshold is from $\pm 20\text{mV}$ to $\pm 320\text{mV}$. The reference can be set by an external voltage source or the 100 μA internal current source flowing through an external resistor. The fail-safe function (missing VDD1 detection) simplifies system-level design and diagnostics. The NSI22C12 supports reinforced isolation with SOW8 wide body package.

Key Features

- Up to 5000V_{RMS} Insulation Voltage
- 3.1V to 27V wide input side power supply
- Adjustable input reference threshold:
 - $\pm 20\text{mV}$ to $\pm 320\text{mV}$
- Analog input voltage range: $\pm 0.4\text{V}$
- Internal threshold reference: 100 μA $\pm 2\%$ error (Max)
- Accurate trigger threshold: $\pm 1\%$ error (Max)
- Fast propagation time: 300ns (Max)
- High CMTI: 150kV/ μs (Typ)
- System-Level Diagnostic Features:
 - VDD1 monitoring

- Operation Temperature: -40°C ~ 125°C
- AEC-Q100 qualified for automotive applications: Grade 1
- RoHS-Compliant Packages:
 - SOW8 wide body (SOP8 300mil)

Safety Regulatory Approvals

- UL recognition:
 - SOW8: 5000V_{rms} for 1 minute per UL1577
- CQC certification per GB4943.1
- CSA component notice 5A
- DIN EN IEC 60747-17 (VDE 0884-17)

Applications

- On Board Chargers
- DC/DC Converters
- Charging Piles
- Traction Inverters

Device Information

Part Number	Package	Body Size
NSI22C12-Q1SWVR	SOW8(300mil)	5.85mm × 7.50mm

Functional Block Diagrams

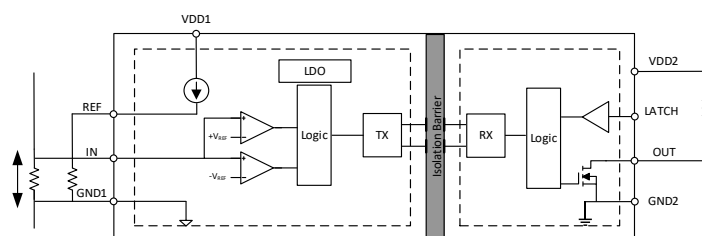


Figure 1. NSI22C12 Block Diagram

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1. Pin Configuration and Functions

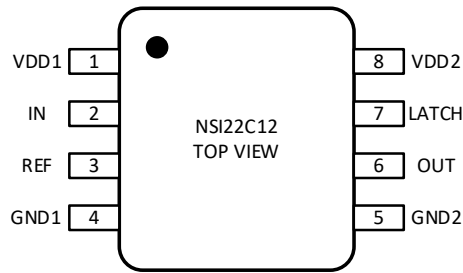


Figure 1.1 NSI22C12 Package

Table 1.1 NSI22C12 Pin Configuration and Description

NSI22C12 PIN NO.	SYMBOL	FUNCTION
1	VDD1	Power supply for input side (3.1V to 27V)
2	IN	Analog input (Bidirectional)
3	REF	Internal reference current output (threshold voltage is $\pm 20 \sim \pm 320 \text{mV}$)
4	GND1	Ground 1, the ground reference for input side
5	GND2	Ground 2, the ground reference for output side
6	OUT	Open-drain output
7	LATCH	Latch enable (active high, this pin can be left floating or tied to GND2 if not used)
8	VDD2	Power supply for output side (2.7V to 5.5V)

2. Absolute Maximum Ratings⁽¹⁾

Parameters	Symbol	Min	Typ	Max	Unit
Input Side Power Supply Voltage (VDD1 to GND1)	VDD1	-0.3		35	V
Output Side Power Supply Voltage (VDD2 to GND2)	VDD2	-0.3		6.5	V
Input Voltage	IN	GND1-6		5.5	V
Reference Voltage	REF	GND1-0.5		6.5	V
Output Voltage	OUT	GND2-0.5		VDD2+0.5	V
Input current per IO pin	I _{IN}	-10		10	mA
Junction Temperature	T _J	-40		150	°C
Storage Temperature	T _{STG}	-55		150	°C

(1) The device cannot operate beyond the listed Absolute Maximum Ratings to prevent permanent device damage. The device is not fully functional if operating outside the Recommended Operating Conditions but within the Absolute Maximum Ratings. Long-time stress of the absolute maximum conditions may affect the device lifetime.

3. ESD Ratings⁽¹⁾

Parameters	Test Condition	Value	Unit
Electrostatic discharge	Human body model (HBM), per AEC-Q100-002-RevD	±2.0	kV
	Charged device model (CDM), per AEC-Q100-011-RevB	±1.0	kV

(1) Though this device features proprietary protection circuitry, proper ESD precautions should be considered to avoid performance degradation of damage due to high energy ESD event. Charged devices and circuit boards may discharge without detection.

4. Recommended Operating Conditions

Parameters	Symbol	Min	Typ	Max	Unit
Power Supply					
Side1 Power Supply	VDD1	3.1	5.0	27	V
Side2 Power Supply	VDD2	2.7	3.3	5.5	V
Input Configuration					
Window threshold voltage	V _{REF} ⁽¹⁾	20		320	mV
Analog input voltage	V _{IN} ⁽²⁾	-0.4		0.4	V
Filter capacitance on REF pin	C _{REF}		15		nF
Latch pin voltage	Latch	0		VDD2	V
Output Configuration					
Output voltage	V _{out}	0		VDD2	V
Output current limit per OUT pin	I _{sink}			12	mA

Parameters	Symbol	Min	Typ	Max	Unit
Temperature					
Operating Ambient Temperature	T _A	-40		125	°C

- (1) Exceeding the recommended VREF will lead to inaccurate reference threshold.
- (2) Exceeding the recommended VIN will lead to leakage current.

5. Thermal Information

Parameters	Symbol	SOW8	Unit
Junction-to-ambient thermal resistance	R _{θJA}	86	°C/W
Junction-to-case (top) thermal resistance	R _{θJC(top)}	28	°C/W
Junction-to-board thermal resistance	R _{θJB}	42	°C/W
Junction-to-top characterization parameter	Ψ _{JT}	4	°C/W
Junction-to-board characterization parameter	Ψ _{JB}	42	°C/W

6. Specifications

6.1. Electrical Characteristics: NSI22C12

(VDD1 = 3.1V~27V, VDD2 =2.7V~5.5V, VREF = 20mV ~ 320mV, VIN = -400mV to +400mV, and TA = -40°C to 125°C. Unless otherwise noted, typical values are at VDD1 = 5V, VDD2 = 3.3V, TA = 25°C)

Parameters	Symbol	Min	Typ	Max	Unit	Comments
Power Supply						
Input Side Supply Voltage	VDD1	3.1	5.0	27	V	
Output Side Supply Voltage	VDD2	2.7	5.0	5.5	V	
Input Side Supply Voltage Undervoltage Threshold	VDD1 _{UV+}		2.9		V	rising
	VDD1 _{UV-}		2.8		V	falling
Output Side Supply Voltage Undervoltage Threshold	VDD2 _{UV+}		2.3		V	rising
	VDD2 _{UV-}		2.1		V	falling
Input Side Supply Current	IDD1		2.4	5	mA	
Output Side Supply Current	IDD2		1.4	4 ⁽¹⁾	mA	R _{PULLUP} =4.7kΩ
Analog Input and Output						
REF Window threshold	VREF	20		320	mV	Falling input threshold
REF threshold error	E _{REF}	-1		1	%	VREF=320mV
Internal REF current source	I _{REF}	98	100	102	μA	
Input hysteresis voltage	V _{HYS}		3.5		mV	Rising input threshold - Falling input threshold
Input resistance	R _{IN}		1		GΩ	At VIN pin
Input bias current	I _{BIAS}		10		pA	VIN=-400mV to +2V

Parameters	Symbol	Min	Typ	Max	Unit	Comments
Input capacitance	C_{IN}		2		pF	At V_{IN} pin
Latch high-level input voltage	Latch V_{IH}	2		$V_{DD2}+0.3$	V	
Latch low-level input voltage	Latch V_{IL}	-0.3		1	V	
Low-level output voltage	V_{OL}	0		$GND1+0.7$	V	
Output leakage current	I_{LKG}		10	300	nA	$V_{PULLUP}=5V$
Output sink current ⁽²⁾	I_{sink}			12	mA	$V_{DD2}=5V$, sinking
Common-mode transient immunity	CMTI	75	150		kV/ μ s	$R_{PULLUP}=10k\Omega$
Timing						
Deglitch time ⁽³⁾	t_d		60		ns	$V_{od}=10mV$, $C_L=15pF$
Propagation delay ⁽³⁾	t_{PD}		150	300	ns	$V_{od}=10mV$, $C_L=15pF$
Output fall time	t_f		2		ns	$C_L=15pF$
VDD1 Blanking time	t_{bik}		200		μ s	
VDD1 Failsafe delay time	t_{fd}		100		μ s	
VDD1 startup time	t_{s1}		50		μ s	VDD1 step to 3.1V, $V_{DD2}\geq 3.0V$
VDD2 startup time	t_{s2}		10		μ s	VDD2 step to 3.0V, $V_{DD1}\geq 3.1V$

- (1) The output supply current is tested with the open-drain output pulled up to the supply voltage.
- (2) The sink current range of the open-drain output to satisfy the low-level output voltage range, 0~ $GND1+0.7$ V.
- (3) The Deglitch time and Propagation delay are tested with V_{IN} rising from V_{REF} to $V_{REF} + V_{od}$ (for the positive comparator) or falling from $-V_{REF}$ to $-V_{REF}-V_{od}$ (for the negative comparator).

6.2. Timing Diagrams

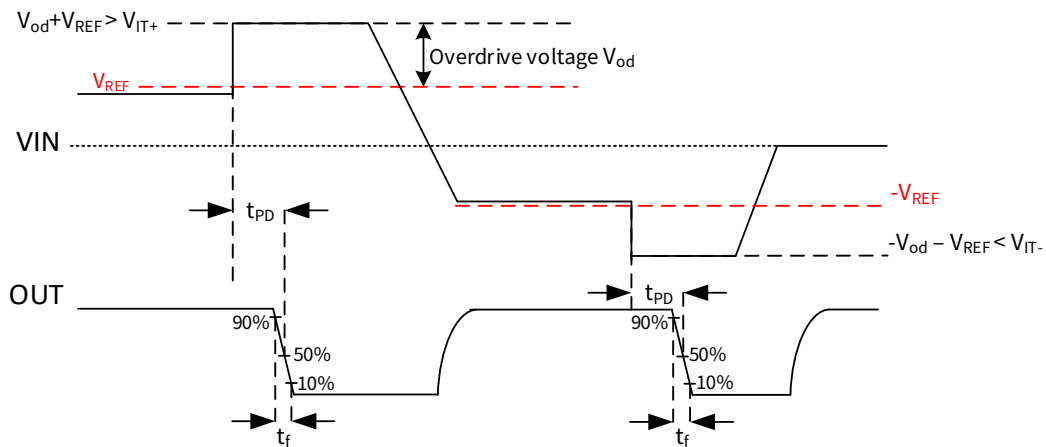


Figure 6.1 Propagation Delay and Output Fall Time Definition

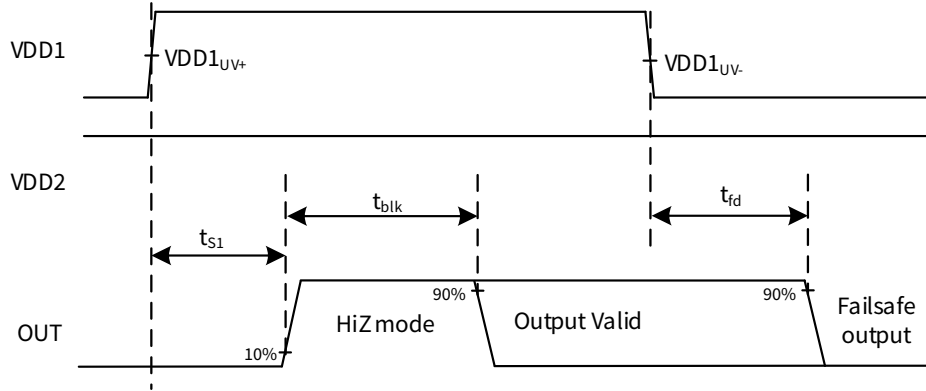


Figure 6.2 VDD1 Startup and Failsafe Process

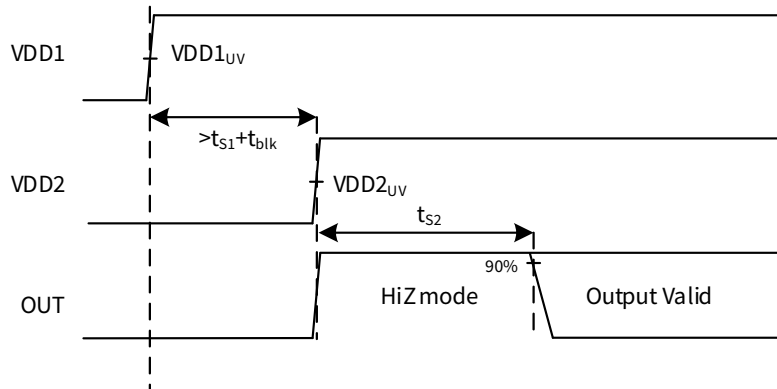


Figure 6.3 VDD2 Startup Process

6.3. Typical Performance Characteristics

Unless otherwise noted, test at VDD1 = 5V, VDD2 = 3.3V, V_{IN} = 0V, V_{REF} = 320mV, T_A = 25°C.

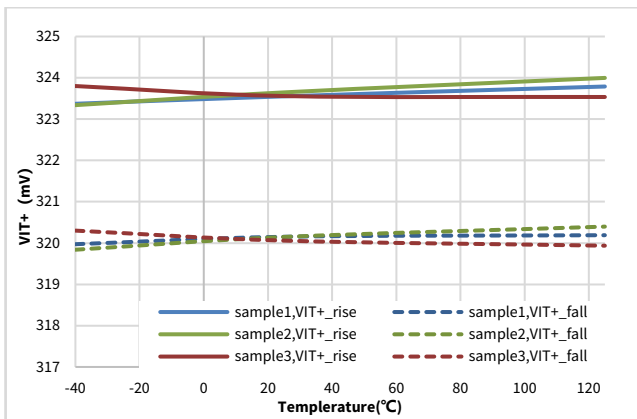


Figure 6.4 Trip Threshold of Positive Comparator vs Temperature

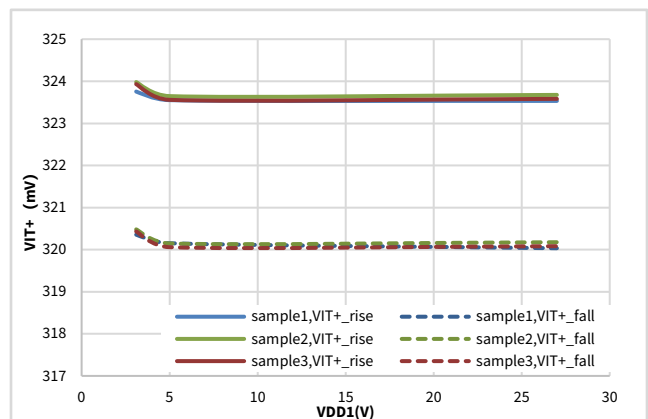


Figure 6.5 Trip Threshold of Positive Comparator vs Input Side Supply Voltage

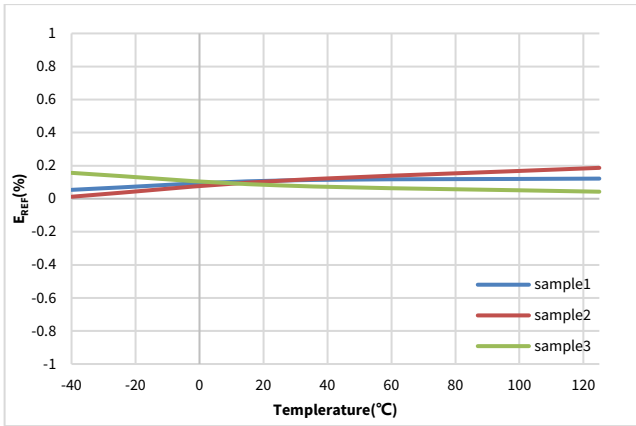


Figure 6.6 E_{REF} of Positive Comparator vs Temperature

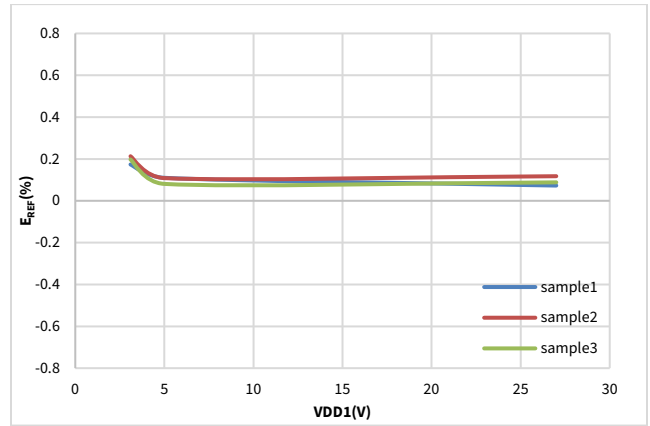


Figure 6.7 E_{REF} of Positive Comparator vs Input Side Supply Voltage

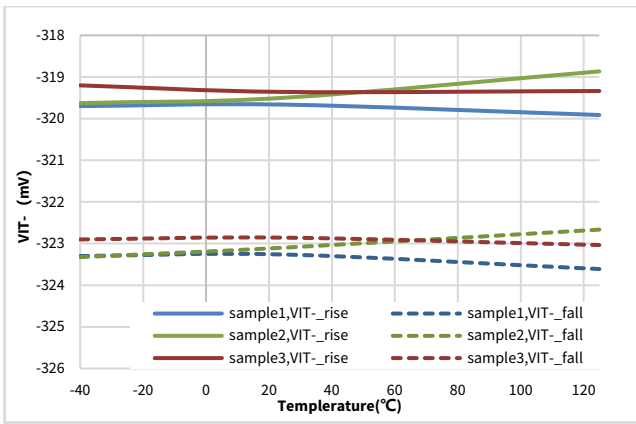


Figure 6.8 Trip Threshold of Negative Comparator vs Temperature

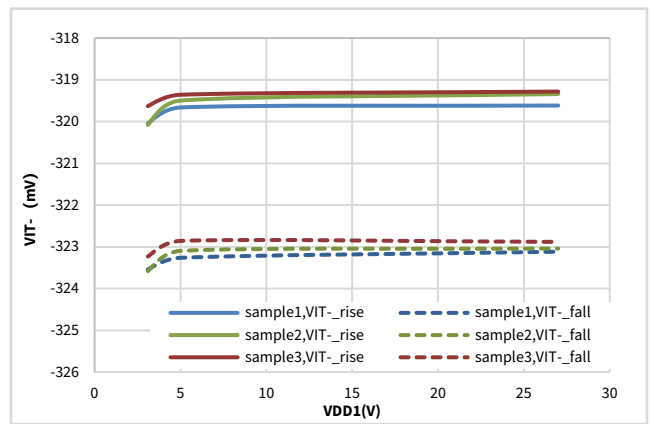


Figure 6.9 Trip Threshold of Negative Comparator vs Input Side Supply Voltage

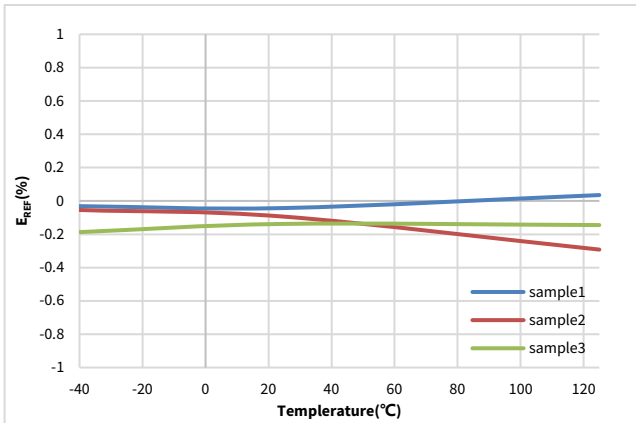


Figure 6.10 E_{REF} of Negative Comparator vs Temperature

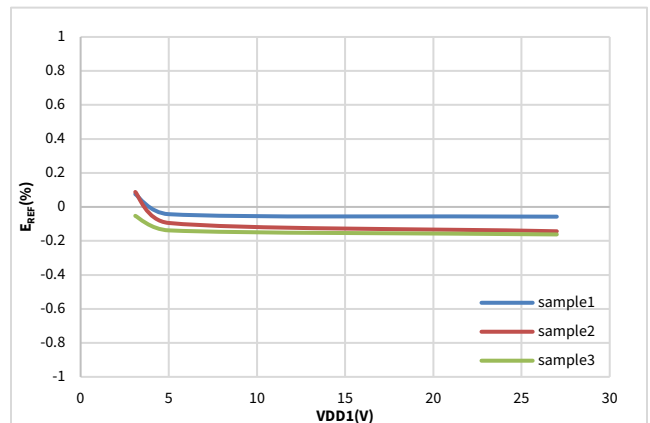


Figure 6.11 E_{REF} of Negative Comparator vs Input Side Supply Voltage

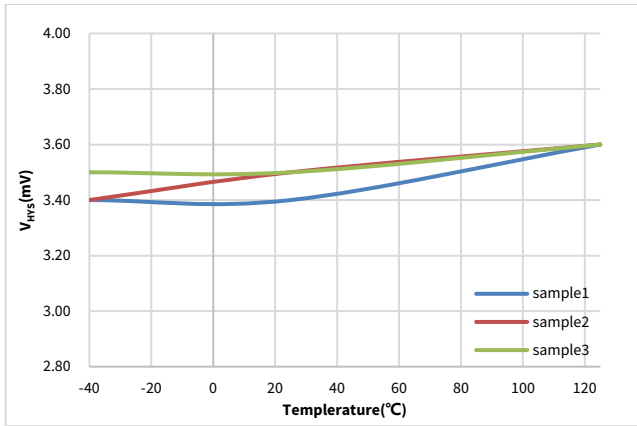


Figure 6.12 V_{HYS} of Positive Comparator vs Temperature

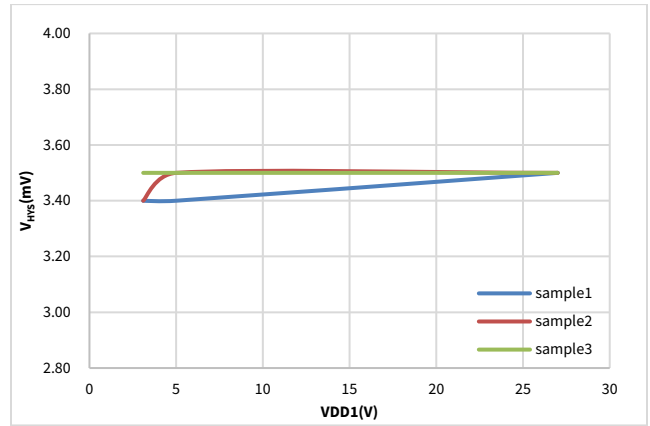


Figure 6.13 V_{HYS} of Positive Comparator vs Input Side Supply Voltage

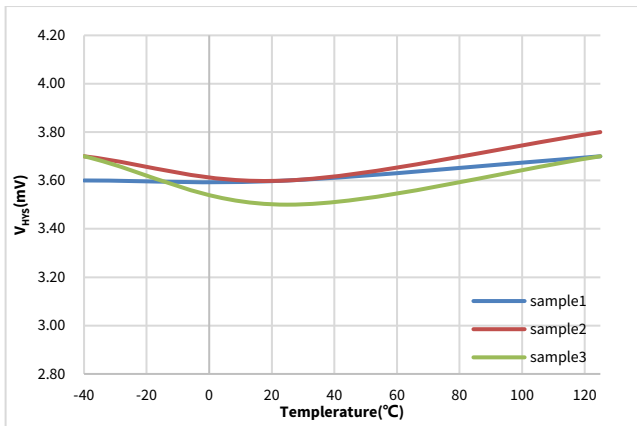


Figure 6.14 V_{HYS} of Negative Comparator vs Temperature

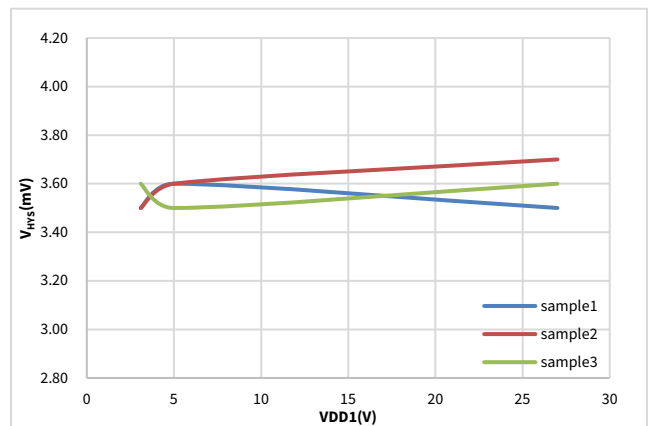


Figure 6.15 V_{HYS} of Negative Comparator vs Input Side Supply Voltage

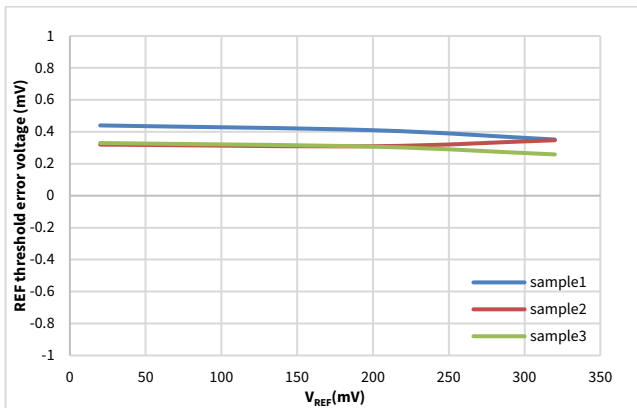


Figure 6.16 REF threshold error voltage of Positive Comparator vs V_{REF}

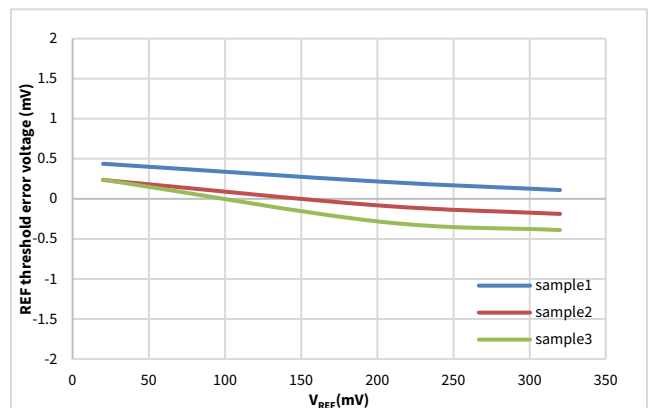


Figure 6.17 REF threshold error voltage of Negative Comparator vs V_{REF}

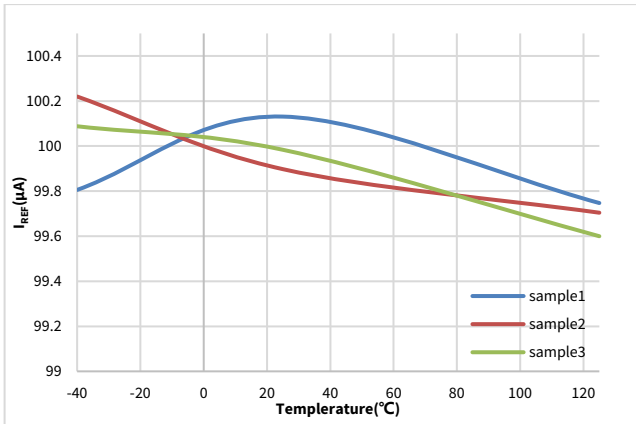


Figure 6.18 I_{REF} vs Temperature

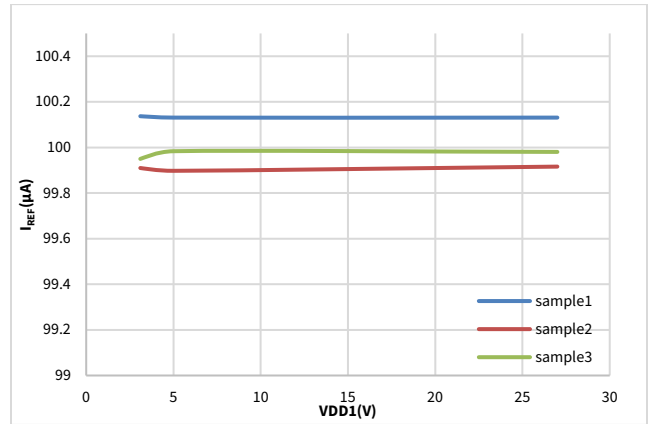


Figure 6.19 I_{REF} vs Input side Supply Voltage

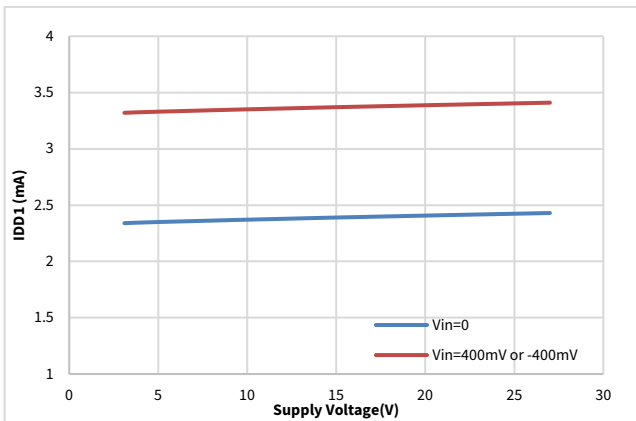


Figure 6.20 IDD1 vs Supply Voltage

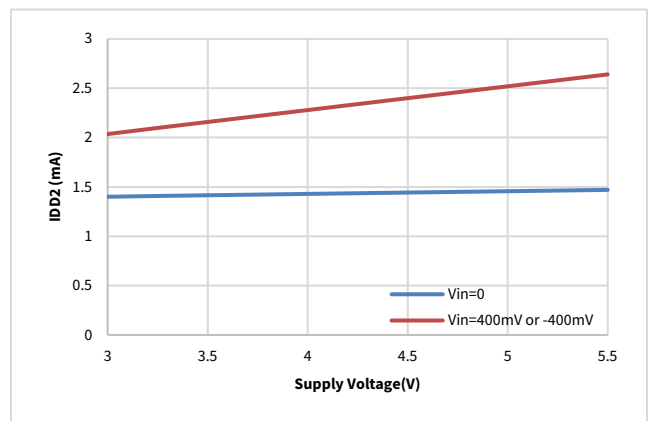


Figure 6.21 IDD2 vs Supply Voltage

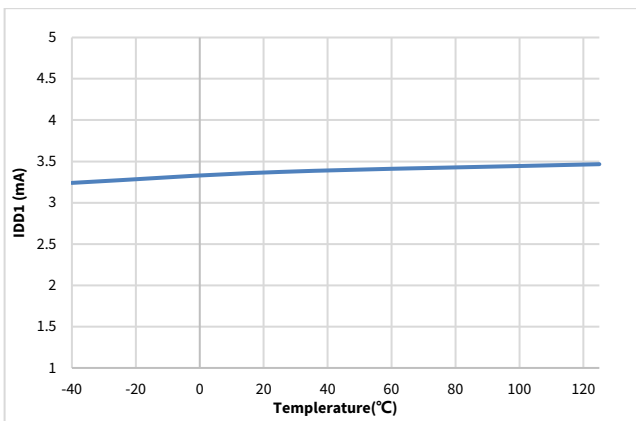


Figure 6.22 IDD1 vs Temperature (V_{in}=400mV)

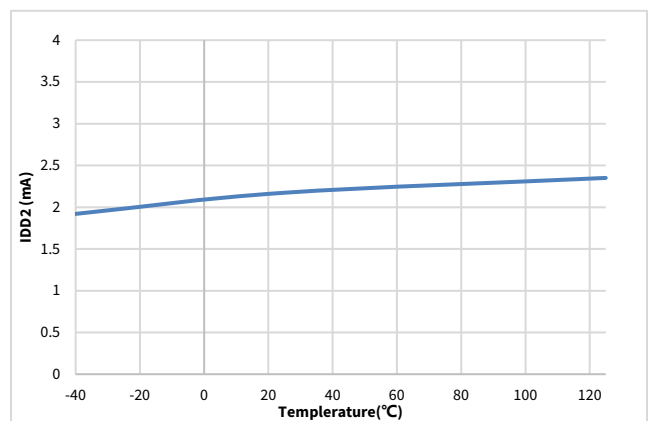


Figure 6.23 IDD2 vs Temperature (V_{in}=400mV)

7. High Voltage Feature Description

7.1. Insulation and Safety Related Specifications

Parameters	Symbol	Value	Unit	Comments
Minimum External Clearance	CLR	8	mm	IEC 60664-1:2007
Minimum External Creepage	CPG	8	mm	IEC 60664-1:2007

Parameters	Symbol	Value	Unit	Comments
Distance Through Insulation	DTI	28	μm	Distance through insulation
Tracking Resistance (Comparative Tracking Index)	CTI	>600	V	DIN EN 60112 (VDE 0303-11); IEC 60112
Material Group		I		IEC 60664-1

Description	Test Condition	Value
Overvoltage Category per IEC60664-1	For Rated Mains Voltage ≤ 150Vrms	I to IV
	For Rated Mains Voltage ≤ 300Vrms	I to IV
	For Rated Mains Voltage ≤ 600Vrms	I to IV
	For Rated Mains Voltage ≤ 1000Vrms	I to III
Climatic Classification		40/125/21
Pollution Degree per DIN VDE 0110		2

7.2. Insulation Characteristics

Description	Test Condition	Symbol	Value	Unit
DIN EN IEC 60747-17 (VDE 0884-17)				
Maximum repetitive isolation voltage		V_{IORM}	2121	V_{PEAK}
Maximum working isolation voltage	AC Voltage	V_{IOWM}	1500	V_{RMS}
	DC Voltage		2121	V_{DC}
Apparent Charge	Method a, after Input/output safety test subgroup 2/3, $V_{ini}=V_{IOTM}$, $t_{ini} = 60\text{ s}$, $V_{pd(m)}=1.2*V_{IORM}$, $t_m=10\text{s}$.	q_{pd}	<5	pC
	Method a, after environmental tests subgroup 1, $V_{ini}=V_{IOTM}$, $t_{ini}=60\text{s}$, $V_{pd(m)}=1.6*V_{IORM}$, $t_m=10\text{s}$			pC
	Method b, routine test (100% production) and preconditioning (type test); $V_{ini}=1.2*V_{IOTM}$, $t_{ini}=1\text{s}$ $V_{pd(m)}=1.875*V_{IORM}$, $t_m=1\text{s}$ (method b1) or $V_{pd(m)}=V_{ini}$, $t_m=t_{ini}$ (method b2)			pC
Maximum transient isolation voltage	$t = 60\text{sec}$	V_{IOTM}	8000	V_{PEAK}
Maximum impulse voltage	Tested in air, 1.2/50us waveform per IEC62368-1	V_{IMP}	6250	V_{PEAK}

Description	Test Condition	Symbol	Value	Unit
Maximum Surge Isolation Voltage	Test method per IEC62368-1, 1.2/50us waveform, $V_{IOSM} \geq V_{IMP} \times 1.3$	V_{IOSM}	10000	V_{PEAK}
Isolation resistance	$V_{IO} = 500V, T_{amb} = 25^{\circ}C$	R_{IO}	$>10^{12}$	Ω
	$V_{IO} = 500V, 100^{\circ}C \leq T_{amb} \leq 125^{\circ}C$	R_{IO}	$>10^{11}$	Ω
	$V_{IO} = 500V, T_{amb} = T_s$	R_{IO}	$>10^9$	Ω
Isolation capacitance	$f = 1MHz$	C_{IO}	0.8	pF
Safety total power dissipation	$V_I = 5.5V, T_J = 150^{\circ}C, T_A = 25^{\circ}C$	P_s	1453	mW
Safety input, output, or supply current	$\theta_{JA} = 86^{\circ}C/W$ for SOW8, $V_I = 5.5V, T_J = 150^{\circ}C, T_A = 25^{\circ}C$	I_s	264	mA
Maximum safety temperature		T_s	150	$^{\circ}C$
UL1577				
Insulation voltage per UL	$V_{TEST} = V_{ISO}, t = 60$ s (qualification), $V_{TEST} = 1.2 \times V_{ISO}, t = 1$ s (100% production test)	V_{ISO}	5000	V_{RMS}

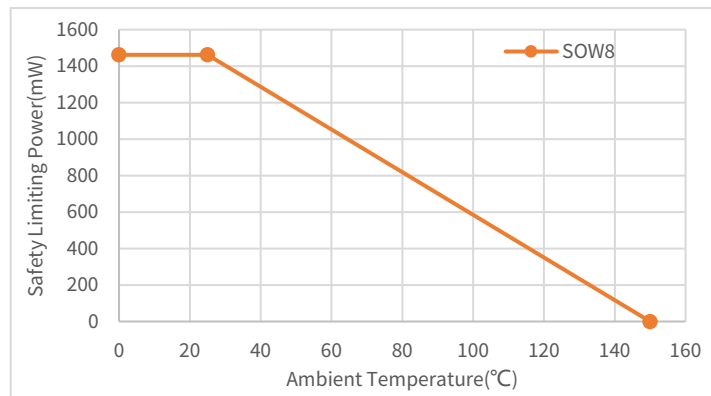


Figure 7.1 NSI22C12 Thermal Derating Curve, Dependence of Safety Limiting Values with Case Temperature per DIN VDE 0884-17

7.3. Regulatory Information

The NSI22C12-Q1SWVR are approved or pending approval by the organizations listed in table.

UL	VDE	CQC	TUV
UL 1577 Component Recognition Program	Approved under CSA Component Acceptance Notice 5A	DIN EN IEC 60747-17 (VDE 0884-17)	Certified according to GB4943.1
Single Protection, 5000V _{rms} Isolation voltage	Single Protection, 5000V _{rms} Isolation voltage	Reinforce Insulation $V_{IORM} = 2121 V_{PEAK}$ $V_{IOTM} = 8000 V_{PEAK}$ $V_{IOSM} = 10000 V_{PEAK}$	Reinforced insulation
E500602	E500602	File (pending)	5000Vrms for 1min
		File (pending)	R50574061

8. Function Description

8.1. Overview

The NSI22C12 is a high-speed basic or reinforced isolated comparator with adjustable internal reference threshold. It is a window comparator with open-drain output and latch function, as shown in the Figure 8.1. The input stage of the device drives a comparator to convert input signal to binary signal. The internal reference threshold can be adjusted by changing the external resistance that internal current source flows through. The drivers (called TX in the Functional Block Diagram) transfer the output of the comparator across the isolation barrier that separates the input side and output side voltage domains. For NSI22C12, the received binary signals are processed and output in the open-drain form. When the Latch pin is set at logic high level, the output is latched and keeps the current level regardless of the input voltage.

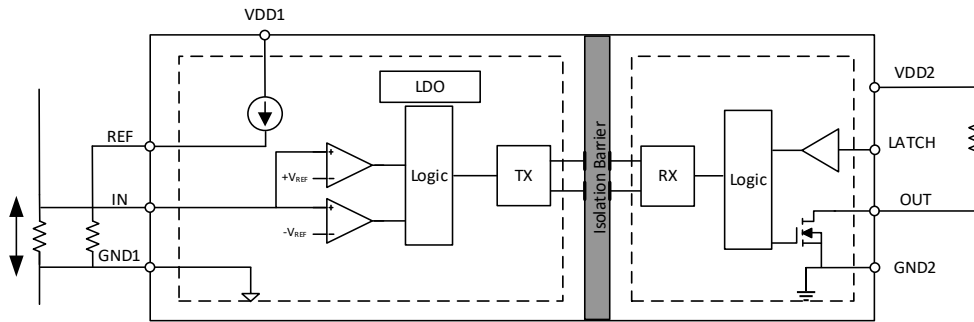


Figure 8.1 Function Block Diagram of NSI22C12

8.2. Analog input

The NSI22C12 is a window comparator with input range from -400mV to +400mV and the comparison window is centered around 0V. The output is pulled down when the input voltage exceeds the comparison window and releases when the input voltage falls back inside the window.

8.3. Reference input

The voltage of REF pin V_{REF} determines the internal reference threshold of the comparator. There are two ways to set V_{REF} . It is recommended to place an external resistor between the REF pin to GND1. The 100 μ A internal current source flows through the external resistor, which generates a high precision voltage reference. In addition, REF pin can be driven by an external voltage source to set the internal reference threshold. NSI22C12 has a window threshold from ± 20 mV to ± 320 mV. Do not drive REF pin outside the recommended range to avoid the unintentional output.

Place a 15nF external capacitor between the REF pin to GND1 to filter the voltage of REF pin. When powered up, the capacitor is charged by the 100 μ A internal current source to V_{REF} . The output is not valid until charging is completed. The larger the capacitance, the longer V_{REF} settling time. If V_{REF} settling time exceeds the sum of VDD1 startup time t_{S1} and blanking time t_{blk} , there will be an invalid output until V_{REF} reaches the expected value, as is shown in Figure 8.2. If the system has additional design for setup blanking time, larger filter capacitance of the REF pin can be selected for better filtering effect without false alarm.

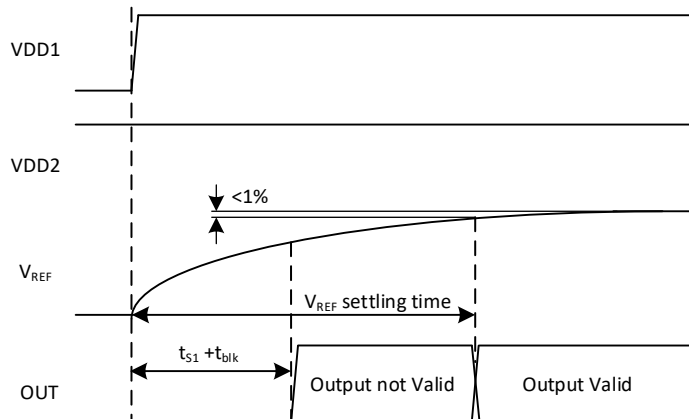


Figure 8.2 Output during V_{REF} Settling Time

8.4. Digital Output

The switching characteristics of NSI22C12 are shown in Figure 8.3.

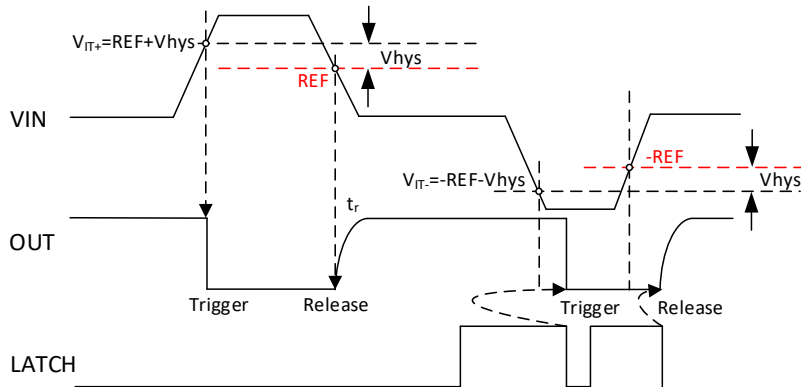


Figure 8.3 Switching Characteristic and Latch Function of NSI22C12

The NSI22C12 is a window comparator with an open-drain output and the comparison window is centered around 0V. For the positive comparator, the output is pulled down when the input voltage rises above the positive trigger threshold voltage $V_{IT+} = V_{REF} + V_{HYS}$ and releases when the input voltage falls below V_{REF} . For the negative comparator, the output is pulled down when the input voltage falls below the negative trigger threshold voltage $V_{IT-} = -V_{REF} - V_{HYS}$ and releases when the input voltage rises above $-V_{REF}$. The hysteresis voltage V_{HYS} (typical value of 3.5mV) makes the comparator have better immunity in noisy environment without the need to add a positive feedback circuit to create hysteresis. With optional latch function, the open-drain output is latched if the Latch pin is set at logic high level, as described in Section 8.5.

It should be noted that the CMTI (Common-mode transient immunity) performance of the open-drain output is related to the pullup resistance and load capacitance. When a common-mode transient event with high dV/dt occurs, the open-drain output may be pulled down because of interference signal coupled from parasitic capacitance between the high side and the low side. The lower pullup resistance enhances immunity. Additionally, a capacitor can be placed between the open-drain output pin and GND2 pin to improve the CMTI performance. However, the load capacitance extends the output fall time and is preferably less than 1nF.

In addition, NSI22C12 integrates some diagnostic measures and offers a failsafe output to simplify system-level design. The failsafe output is low-level voltage and it will be activated when the undervoltage of VDD1 is detected ($VDD1 < VDD1_{UV}$), as is shown in Figure 8.4. When the undervoltage of VDD2 is detected ($VDD2 < VDD2_{UV}$), the open-drain output is always high as it is pulled up to VDD2 through a resistor.

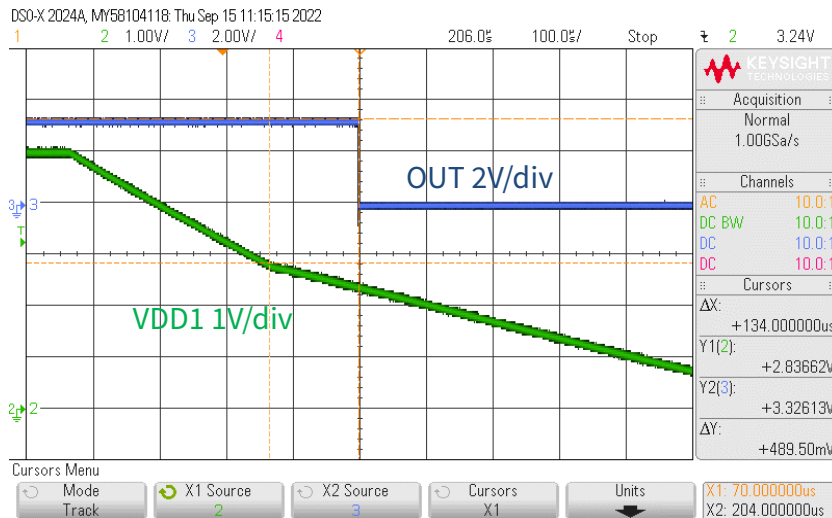


Figure 8.4 Typical Failsafe output when VDD1 undervoltage

8.5. Optional Latch Function

The NSI22C12 provides an optional latch function. When the Latch pin is set at logic low level or floating, the output follows the comparison of the input voltage and the reference voltage. When the Latch pin is set at logic high level, the

output is latched and keeps the gate current level regardless of the input voltage variation. The latch function is shown in Figure 8.3.

9. Application Note

9.1. Typical Application Circuit

The NSI22C12 is highly suitable for over-current, over-voltage, or over-temperature protection application such as AC motor controls because of its short response time. The typical application circuit is shown in Figure 9.1.

The phase currents of the motor drive are sensed by isolated amplifiers such as NSI1300 as control signals. While for current-monitor purpose, NSI22C12 is a better choice for phase current detecting with bidirectional over-current protection and fast response. In addition, phase current monitoring cannot cover all overcurrent faults such as shoot-through of the bridge. Therefore, an extra NSI22C12 is added to monitor the DC bus current, as is shown in Figure 9.1.

The voltage across the shunt resistor R_{shunt} is applied to the input of NSI22C12 through a capacitor filter. An external resistor paralleled with a 15nF capacitor is placed between the REF pin to GND1 to generate the reference voltage of the comparator. The open-drain output is pulled up through a resistor. A capacitor can be placed between the open-drain output pin and GND2 pin to improve the CMTI performance. The latching control signal is provided by the MCU to lock the output.

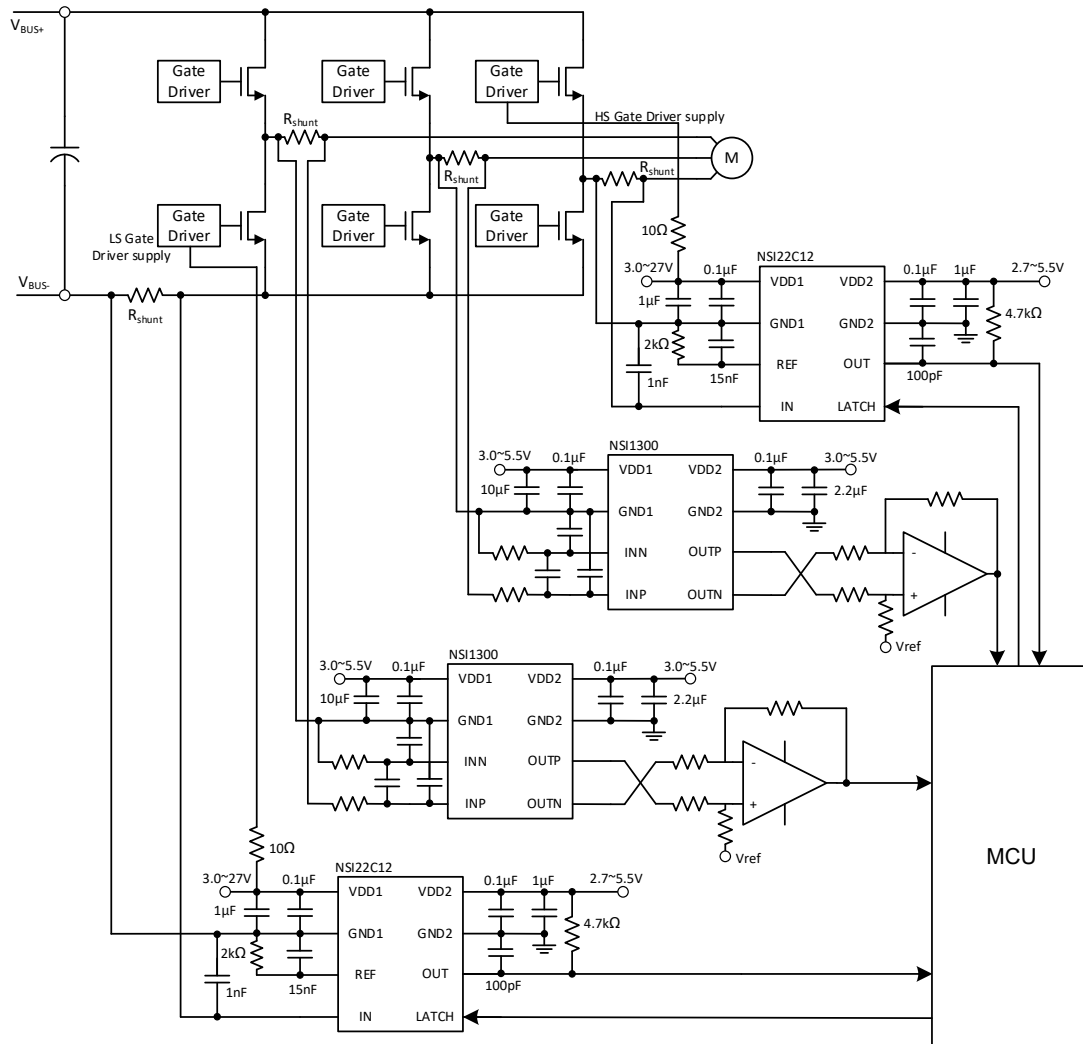


Figure 9.1 Typical application circuit of NSI22C12 in over-current protection

9.2. Power Supply Recommendations

The NSI22C12 requires a $0.1\mu\text{F}$ capacitor paralleled with a $1\mu\text{F}$ capacitor between VDD1 and GND1, VDD2 and GND2 for power supply decoupling.

A 10Ω resistor is recommended in series with the high-side power supply for current limiting and better filtering in the applications that the high side is powered by a noisy high-voltage power supply. For example, for DC bus current monitoring of the motor drive, the LS gate driver supply can be multiplexed as the high-side power supply. For phase current monitoring of the motor drive, the HS gate driver supply can be multiplexed as the high-side power supply.

9.3. PCB Layout

There are some key guidelines or considerations for optimizing performance in PCB layout:

- The NSI22C12 requires a $0.1\mu\text{F}$ bypass capacitor between VDD1 and GND1, VDD2 and GND2. The capacitor should be placed as close as possible to the VDD pin. If better filtering is required, an additional $1\sim 10\mu\text{F}$ capacitor may be used.
- Kelvin rules is recommended for the connection between shunt resistor to the NSI22C12. Because of the Kelvin connection, any voltage drops across the trace and leads should have no impact on the measured voltage.
- Place the shunt resistor close to the IN pin and keep the layout of the input voltage and the sampling GND1 symmetrical and run very close to each other to the input of the NSI22C12. This minimizes the loop area of the connection and reduces the possibility of stray magnetic fields from interfering with the measured signal.
- Place the external reference resistor and its filter capacitor as close as possible to the REF pin for a stable reference voltage.

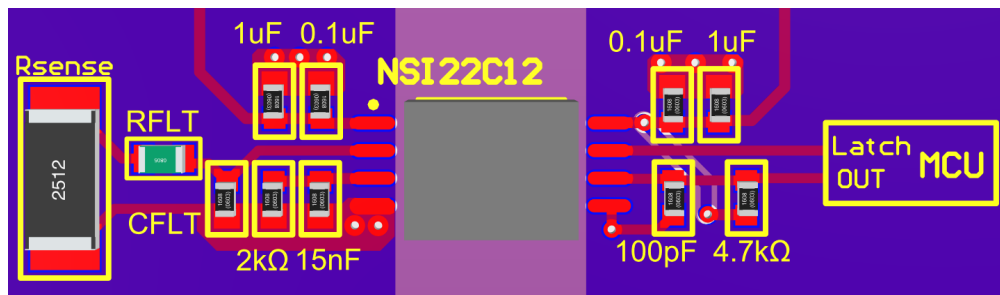
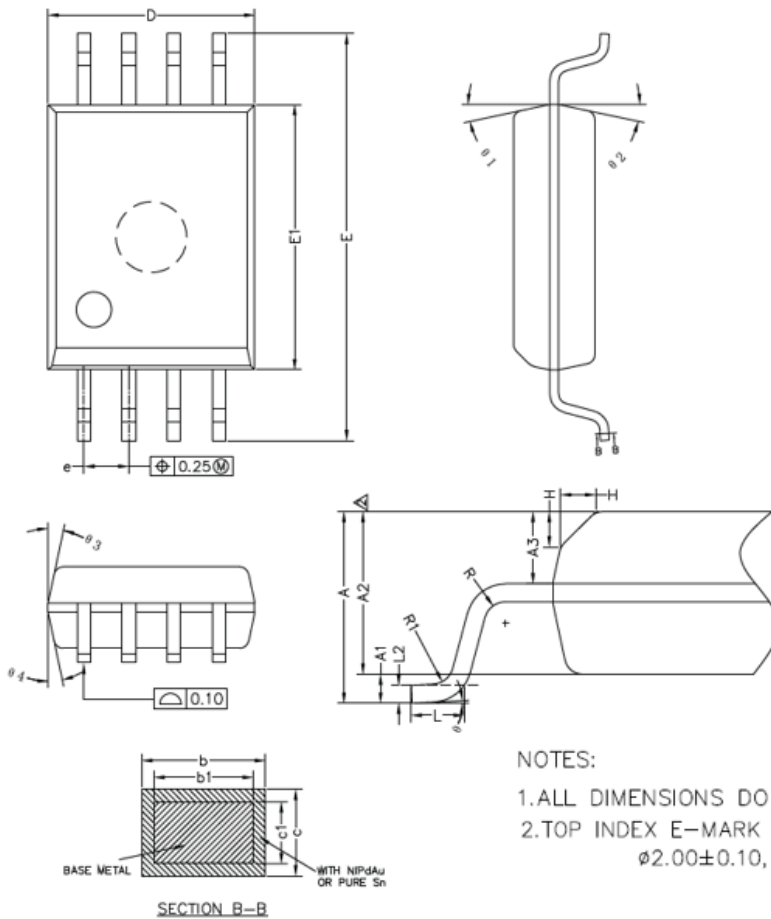


Figure 9.2 PCB layout example of NSI22C12

10. Package Information



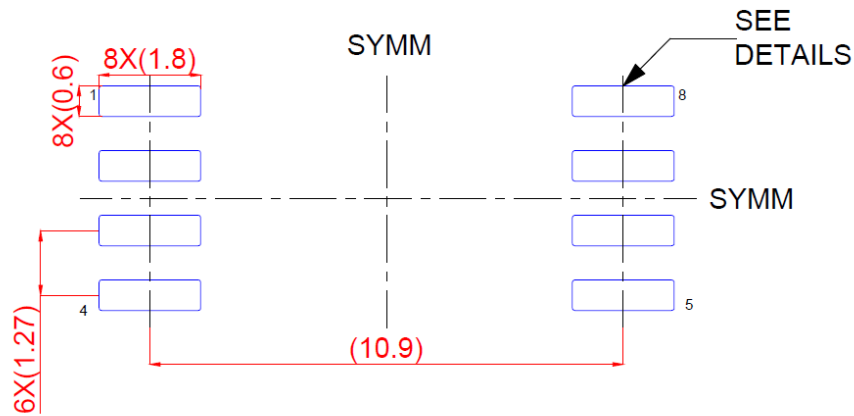
COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	—	—	2.85
A1	0.31	0.41	0.51
A2	2.20	2.30	2.40
A3	0.97	1.02	1.07
b PURE Sn	0.33	—	0.47
NiPdAu	0.33	—	0.44
b1	0.33	0.38	0.43
c PURE Sn	0.22	—	0.32
NiPdAu	0.22	—	0.29
c1	0.22	0.25	0.28
D	5.75	5.85	5.95
E	11.30	11.50	11.70
E1	7.40	7.50	7.60
e	1.17	1.27	1.37
H	0.40	0.50	0.60
L	0.55	0.75	0.90
L1	2.00REF		
L2	0.25BSC		
R	0.07	—	—
R1	0.07	—	—
θ	0°	—	8°
θ_1	10°	12°	14°
θ_2	10°	12°	14°
θ_3	10°	12°	14°
θ_4	10°	12°	14°

NOTES:

1. ALL DIMENSIONS DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS.
2. TOP INDEX E-MARK $\phi 1.00 \pm 0.10$, DEPTH $0.10^{+0.15}_{-0.08}$, BOTTOM E-MARK $\phi 2.00 \pm 0.10$, DEPTH $0.15^{+0.15}_{-0.13}$.

Figure 10.1 SOW8 Package Shape and Dimension in millimeters



LAND PATTERN EXAMPLE(mm)
9.1 mm NOMINAL
CLEARANCE/CREEPAGE

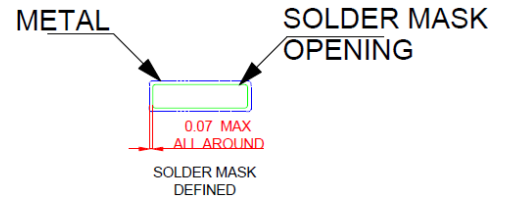
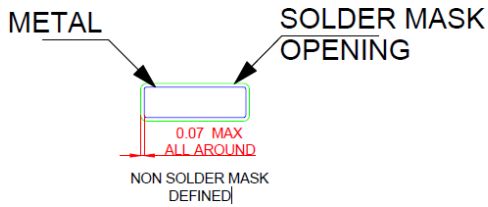


Figure 10.2 SOW8 Package Board Layout Example

11. Ordering Information

Part No.	Isolation Rating(kV)	REF Range(V)	Moisture Sensitivity Level	Temperature	Automotive	Package Type	Package Drawing	SPQ
NSI22C12-Q1SWVR	5	±0.02~±0.32	Level-3	-40 to 125°C	YES	SOP8 (300mil)	SOW8	1000

12. Documentation Support

Part Number	Product Folder	Datasheet	Technical Documents	Isolator selection guide
NSI22C12-Q1	Click here	Click here	Click here	Click here

13. Tape and Reel Information

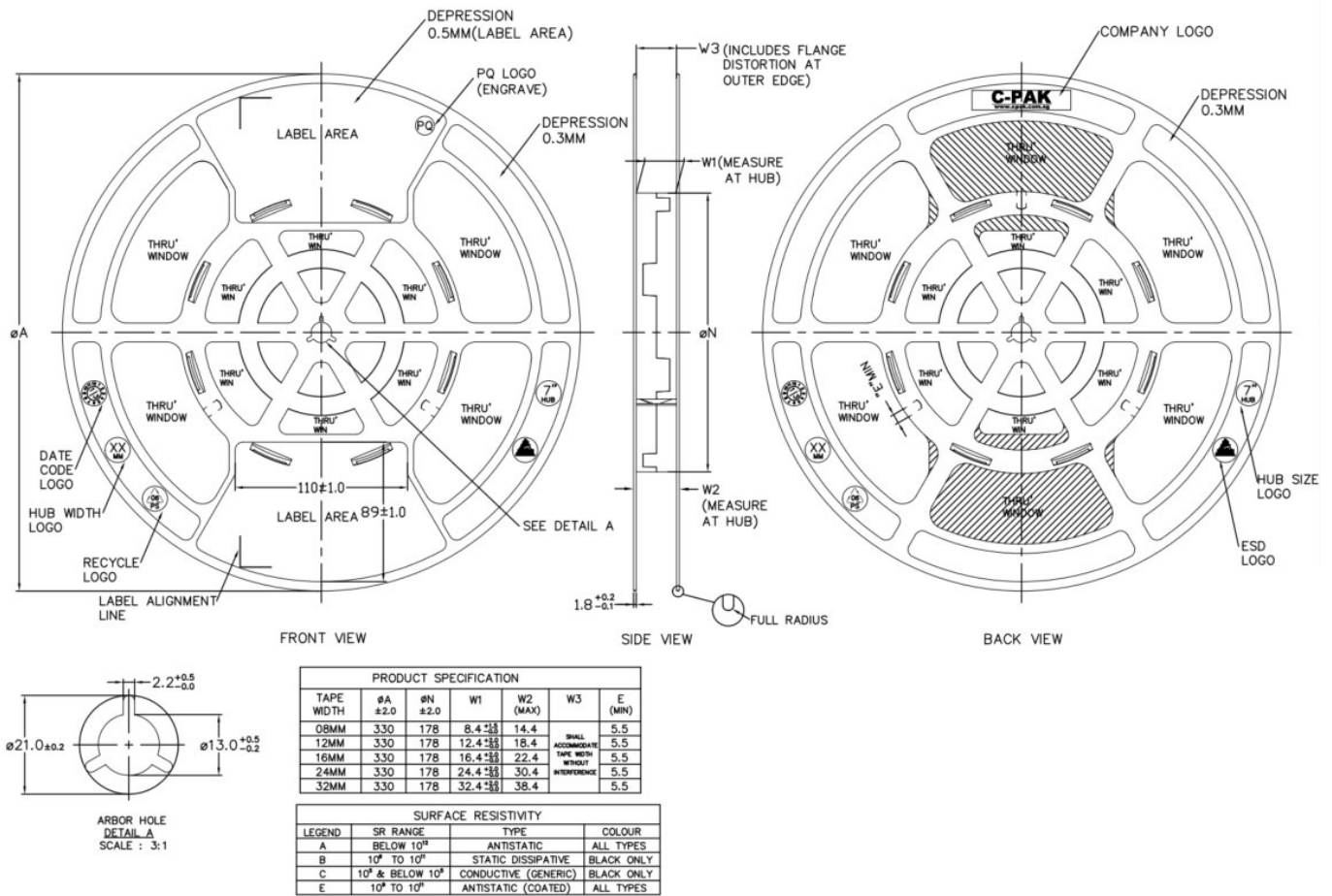


Figure 13.1 Reel Information

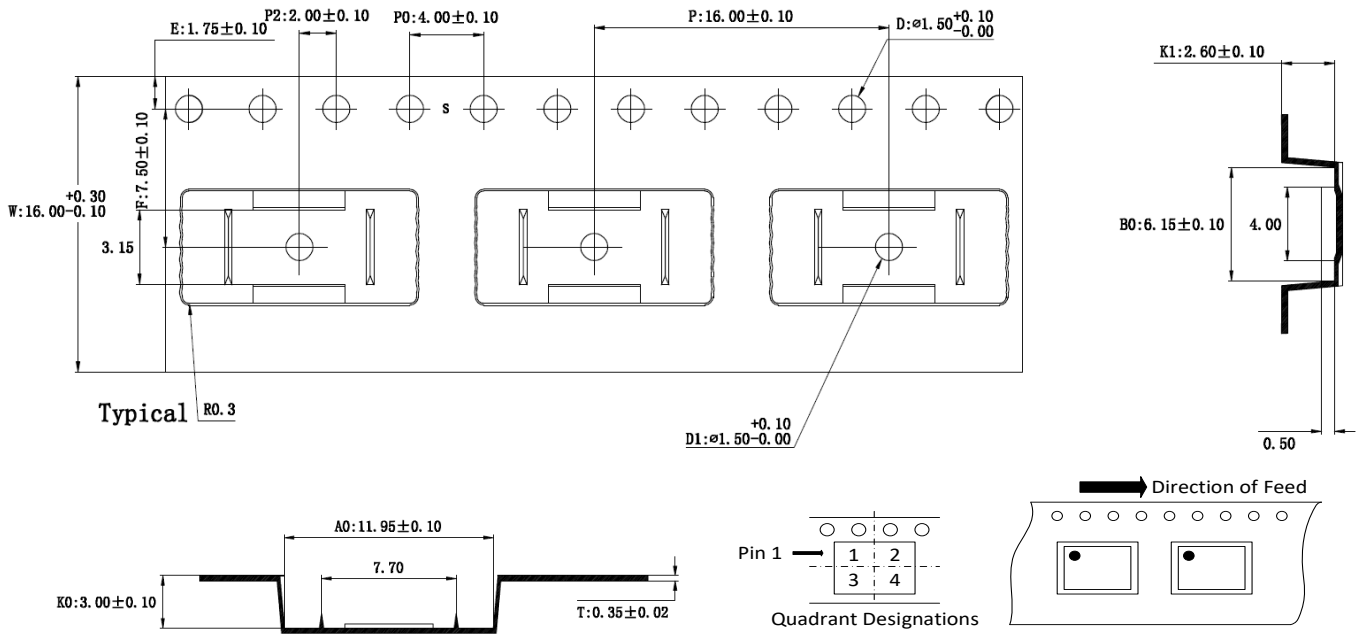


Figure 13.2 Tape Information of SOP8(300mil)

14. Revision History

Revision	Description	Date
1.0	Initial release	2025/1/13
1.1	Update Regulatory Information in 7.3. Update Figure 10.1 SOW8 Package Shape and Dimension in millimeters.	2025/6/17

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